



12N40-CB

Preliminary

Power MOSFET

12A, 400V N-CHANNEL POWER MOSFET

DESCRIPTION

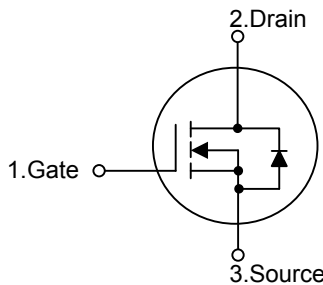
The UTC **12N40** is an N-channel mode power MOSFET using UTC's advanced technology to provide customers with planar stripe and DMOS technology. This technology specializes in allowing a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The UTC **12N40** is universally applied in electronic lamp ballast based on half bridge topology and high efficient switched mode power supply.

FEATURES

- * $R_{DS(ON)} < 0.4\Omega @ V_{GS} = 10V, I_D = 6.0A$
- * High Switching Speed
- * 100% Avalanche Tested

SYMBOL

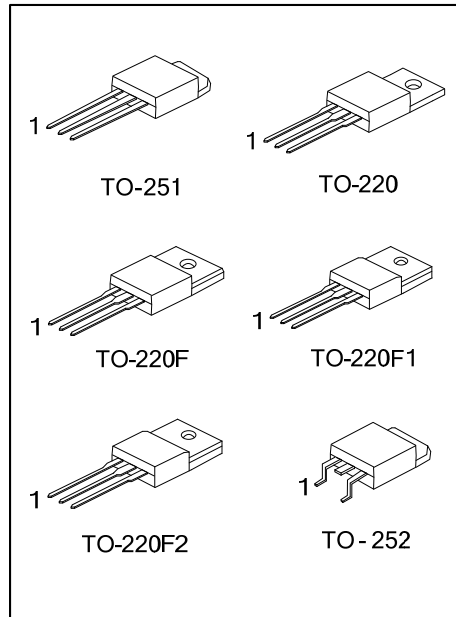


ORDERING INFORMATION

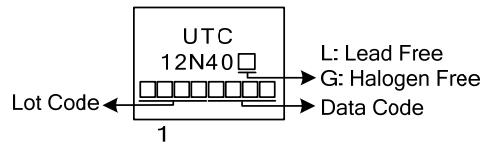
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
12N40L-TA3-T	12N40G-TA3-T	TO-220	G	D	S	Tube
12N40L-TF1-T	12N40G-TF1-T	TO-220F1	G	D	S	Tube
12N40L-TF2-T	12N40G-TF2-T	TO-220F2	G	D	S	Tube
12N40L-TF3-T	12N40G-TF3-T	TO-220F	G	D	S	Tube
12N40L-TM3-R	12N40G-TM3-R	TO-251	G	D	S	Tape Reel
12N40L-TN3-R	12N40G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>12N40L-TA3-T</p>	<p>(1) T: Tube, R: Tape Reel</p> <p>(2) TA3: TO-220, TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2, TM3: TO-251, TN3: TO-252</p> <p>(3) L: Lead Free, G: Halogen Free and Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	400	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current ($T_C=25^\circ\text{C}$)	Continuous	I_D	12	A
	Pulsed (Note 2)	I_{DM}	48	A
Avalanche Current (Note 2)		I_{AR}	7	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	318	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.4	V/ns
Power Dissipation ($T_C=25^\circ\text{C}$)	TO-220	P_D	192	W
	TO-220F/TO-220F1		50	W
	TO-220F2			
	TO-251/TO-252		100	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 13 \text{ mH}$, $I_{AS} = 7.0\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 12\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	PACKAGE	SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-220F1/TO-220F2			
	TO-251/TO-252			
Junction to Case	TO-220	θ_{JC}	0.65	$^\circ\text{C}/\text{W}$
	TO-220F/TO-220F1		2.5	$^\circ\text{C}/\text{W}$
	TO-220F2			
	TO-251/TO-252		1.25	$^\circ\text{C}/\text{W}$

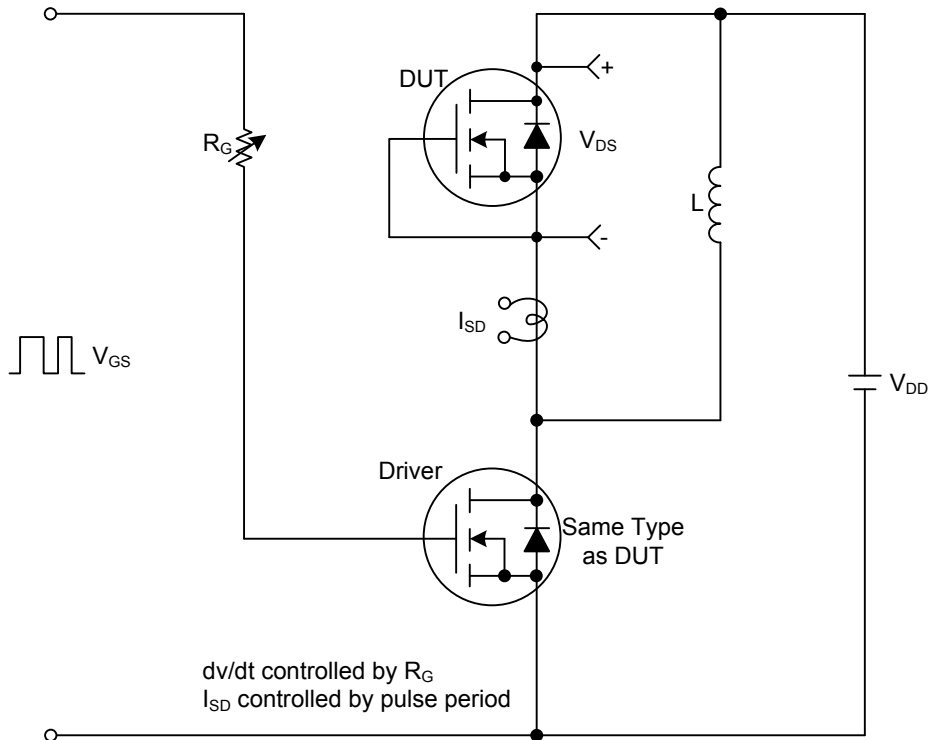
■ ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	400			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=400\text{V}$, $V_{GS}=0\text{V}$			1	μA
Gate- Source Leakage Current	Forward	I_{GSS}			+100	nA
	Reverse				-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=6.0\text{A}$			0.4	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}$, $V_{DS}=25\text{V}$, $f=1.0\text{MHz}$		1670		pF
Output Capacitance	C_{OSS}			170		pF
Reverse Transfer Capacitance	C_{RSS}			150		pF
SWITCHING PARAMETERS						
Total Gate Charge	Q_G	$V_{DS}=50\text{V}$, $V_{GS}=10\text{V}$, $I_D=1.3\text{A}$, $I_G=100\mu\text{A}$ (Note 1, 2)		35		nC
Gate to Source Charge	Q_{GS}			6		nC
Gate to Drain Charge	Q_{GD}			6.5		nC
Turn-ON Delay Time	$t_{D(ON)}$	$V_{DD}=30\text{V}$, $V_{GS}=10\text{V}$, $I_D=0.5\text{A}$, $R_G=25\Omega$ (Note 1, 2)		75		ns
Rise Time	t_R			45		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			260		ns
Fall-Time	t_F			60		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S				12	A
Maximum Body-Diode Pulsed Current	I_{SM}				48	A
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0\text{V}$, $I_S=12\text{A}$			1.4	V
Reverse Recovery Time	t_{rr}	$V_{GS}=0\text{V}$, $I_S=12\text{A}$		300		ns
Reverse Recovery Charge	Q_{rr}	$dI_F/dt=100\text{A}/\mu\text{s}$ (Note 1)		2		μC

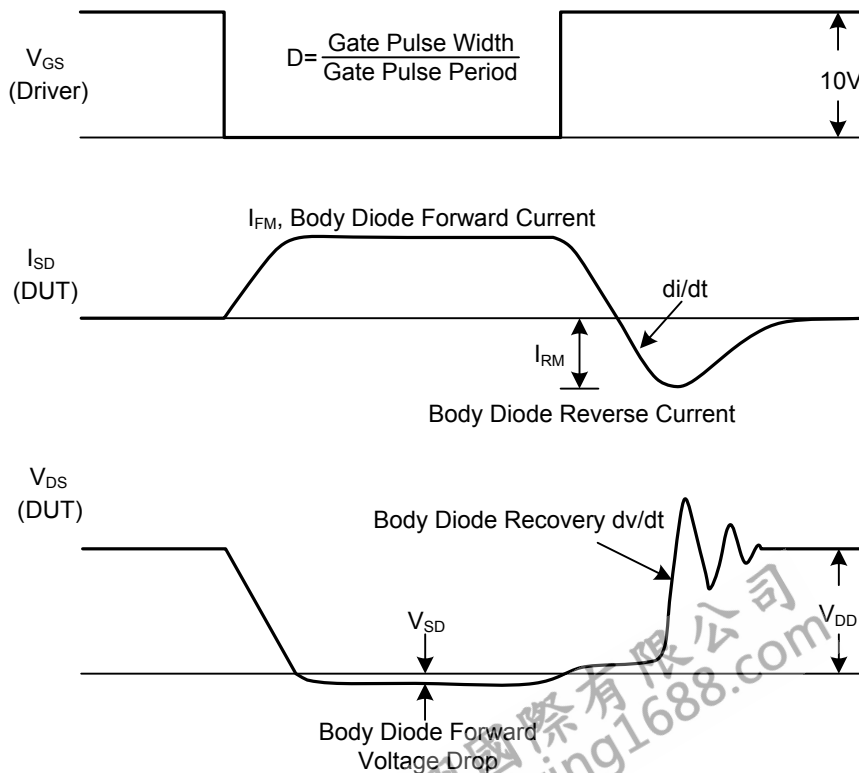
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

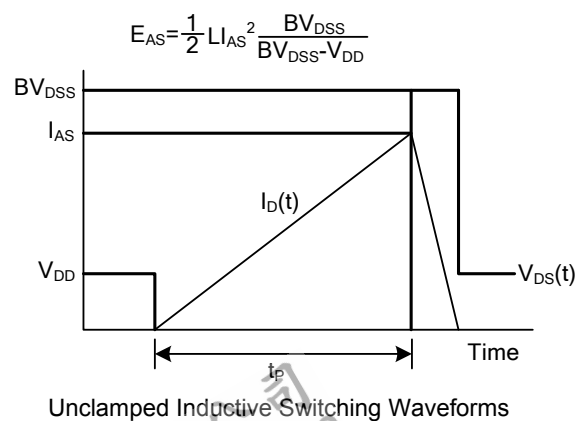
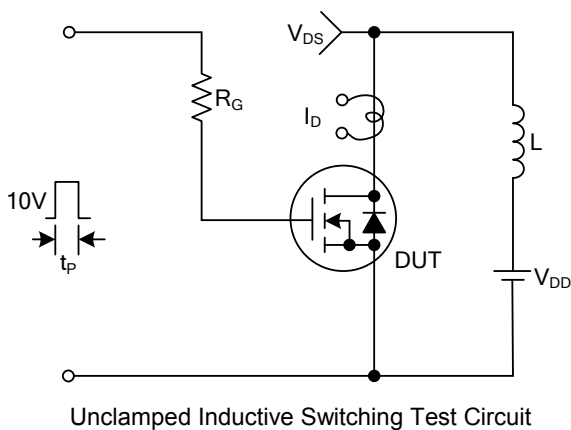
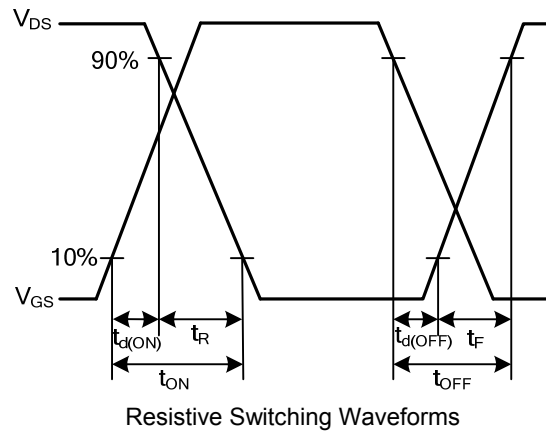
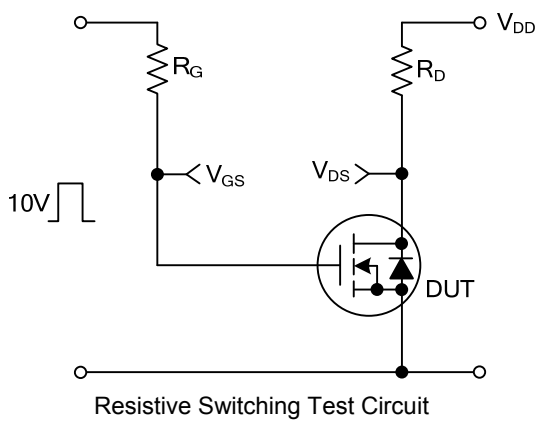
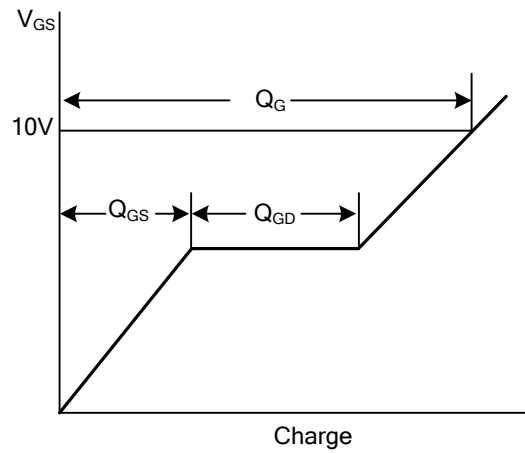
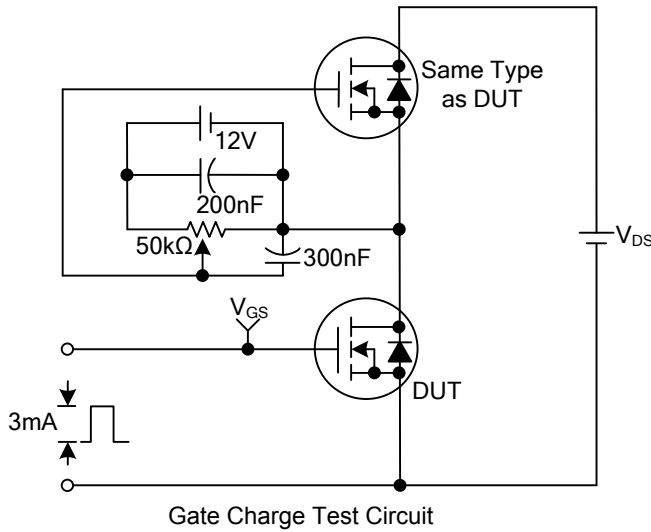
■ TEST CIRCUITS AND WAVEFORMS



Peak Diode Recovery dv/dt Test Circuit & Waveforms



■ TEST CIRCUITS AND WAVEFORMS (Cont.)



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